

a dummy region having a plurality of dummy trench isolation [regions] patterns located between said first and said second regions[; and

a positioning mark which is formed between said plurality of dummy trench isolation regions and which is used for positioning a mask film]

, wherein the dummy trench isolation patterns comprise a pattern which constitutes a positioning mark and extends in a second direction different from the first direction.

2. (Amended) A semiconductor device according to Claim 1, wherein said semiconductor device comprises a memory cell region in which memory cell transistors are formed and a peripheral circuit region in which a peripheral circuit for controlling the operation of said memory cell transistors is formed and wherein said first region includes said memory cell region and said second region includes said peripheral circuit region, wherein the first and second regions are arranged in the first direction and the dummy region extends in the first direction along the first and second regions.

Please cancel claim 3.

Please add new claim 11.

11. (New) The semiconductor device according to claim 1, wherein the pattern of the dummy trench isolation extends in a vertical direction with respect to the first direction.

#### REMARKS

Applicant submits that by the present Amendment and Remarks, this application is placed in clear condition for immediate allowance. At the least, the present Amendment places this application in better condition for Appeal. Accordingly, entry of the present Amendment